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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/807,537	03/23/2004	Yehuda Shekel	06727/0201090-US0 3773		
7590 06/01/2006 D. Morgan Tench 1180 Corte Riviera			EXAMINER		
			CULBERT, ROBERTS P		
Camarillo, CA 93010			ART UNIT	PAPER NUMBER	
•			1763		
			DATE MAILED: 06/01/2006		

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application	on No.	Applicant(s)	
		10/807,53	37	SHEKEL ET AL.	
	Office Action Summary	Examiner		Art Unit	
		Roberts C	ulbert	1763	
Period fo	The MAILING DATE of this communic or Reply	ation appears on the	cover sheet with the c	orrespondence addres	's
WHIC - Exter after - If NO - Failu Any	ORTENED STATUTORY PERIOD FO CHEVER IS LONGER, FROM THE MA nsions of time may be available under the provisions of SIX (6) MONTHS from the mailing date of this community period for reply is specified above, the maximum stature to reply within the set or extended period for reply within	ILING DATE OF TH 37 CFR 1.136(a). In no even inication. story period will apply and wi ill, by statute, cause the app	HIS COMMUNICATION ent, however, may a reply be tin Il expire SIX (6) MONTHS from lication to become ABANDONE	N. nely filed the mailing date of this commun D (35 U.S.C. § 133).	
Status					
2a)	Responsive to communication(s) filed This action is FINAL . 2b Since this application is in condition for closed in accordance with the practice	o)⊠ This action is n or allowance except	for formal matters, pro		rits is
Disnositi	on of Claims				
5)□ 6)⊠ 7)□ 8)□	Claim(s) 1-33 is/are pending in the ap 4a) Of the above claim(s) 1-13 is/are we claim(s) is/are allowed. Claim(s) 14-33 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction	vithdrawn from cons			
	The specification is objected to by the	Evaminor			
10)⊠	The drawing(s) filed on 23 March 2004 Applicant may not request that any objecti Replacement drawing sheet(s) including the source of the country of the cou	! is/are: a)☐ accep on to the drawing(s) b ne correction is require	e held in abeyance. See ed if the drawing(s) is obj	e 37 CFR 1.85(a). jected to. See 37 CFR 1.	` ,
Priority u	inder 35 U.S.C. § 119				
12)⊠ / a)[Acknowledgment is made of a claim fo All b) Some * c) None of: 1. Certified copies of the priority do 3. Copies of the certified copies of application from the International See the attached detailed Office action	ocuments have bee ocuments have bee the priority docume al Bureau (PCT Rule	n received. n received in Application ents have been received e 17.2(a)).	on No ed in this National Stag	je
2) 🔲 Notice	t(s) e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO nation Disclosure Statement(s) (PTO-1449 or PT		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P)
	r No(s)/Mail Date <u>8/13/04</u> .	. 3.02/00)	6) Other:	,,	

DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of invention II (Claims 14-33) in the reply filed on 4/19/06 is acknowledged. Claims 1-13 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected invention, there being no allowable generic or linking claim.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 14-16, 18, 21-24, 26, 28, 32 and 33 are rejected under 35 U.S.C. 102(b) as being anticipated by U.S. Patent 6,203,659 to Shen.

Regarding Claim 14, Shen et al. teach a method for real-time dynamic analysis of chemical etching of a solid in a liquid etchant, comprising the steps of: passing electromagnetic radiation from an electromagnetic radiation source (22) through a liquid etchant (stripper), at least at two points in time, wherein said liquid etchant is operative to etch said solid; performing ex situ non-contact scanning detection over a predetermined spectral range (infared) of said electromagnetic radiation passed through said liquid etchant, by means of a detector (24) over said at least at two points in time so as to detect at least one change in an at least one optical property of said liquid etchant; comparing said at least one change in said at least one optical property at said at least two points in time by means of an algorithm in a processor (26) so as to provide a rate of etching of said solid.

Regarding Claim 15, Shen et al. teach passing includes: emitting electromagnetic radiation in a predetermined spectral range from an electromagnetic radiation source, transmitting said electromagnetic radiation via a first optical transmission element from said electromagnetic radiation source through a

sampling element containing a sample of said liquid etchant, and conveying output electromagnetic radiation from said sample of said liquid etchant via a second optical transmission element to said detector.

Regarding Claim 16, Shen et al. teach that comparing further comprises performing a chemometric manipulation on data relating to at least one change in said at least one optical property to provide the stripper concentration level.

Regarding Claim 18, Shen et al. teach that the algorithm further provides a rate of depletion of at least one chemical component of said liquid etchant over a period of time.

Regarding Claim 21, Shen et al. teaches that passing the liquid etchant through a sampling element having a substantially transparent sampling tube. (C3, L55-65)

Regarding Claim 22-24, Shen et al. teach that the comparing step comprises converting one optical property change into a concentration rate of change of at least one chemical component of the liquid etchant.

Regarding Claim 26, Shen et al. teach detecting a fault in a rate of addition of a replenishing chemical component. (C4, L38-44)

Regarding Claim 28, the method is independent of temperature and the presence of bubbles as claimed by applicant.

Regarding Claim 32, Shen et al. teach determining a concentration of an acid.

Regarding Claim 33, Shen teach an infared light source. (C4, L1-8)

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 14-26, 28 and 30-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over the publication "In-Situ Chemical Concentration Control for Wafer Wet Cleaning" to Brause et al. in view of The publication "Quantification of Hydrofluoric Acid Species by Chemical Modeling Regression of Near-Infrared Spectra" to Thompson et al.

Regarding Claim 14, the publication "In-Situ Chemical Concentration Control for Wafer Wet Cleaning" to Brause et al. teaches that the etching of SiO₂ depends strongly on temperature and HF concentration. (P 315, bottom paragraph) Brause et al. further teach that the etch rate of the SiO₂ may be accurately controlled by controlling HF concentration in the etching process. However, Brause et al. teach measuring conductivity to determine the concentration of HF in the etching process. Brause et al. do not teach optical detection techniques.

However, the publication "Quantification of Hydrofluoric Acid Species by Chemical Modeling Regression of Near-Infrared Spectra" to Thompson et al. teaches that electromagnetic radiation spectroscopy may be used to measure the concentration of HF in aqueous solution. Brause et al. further teach passing electromagnetic radiation from an electromagnetic radiation source through a liquid etchant (hydrofluoric acid), at least at two points in time, wherein said liquid etchant is operative to etch said solid; performing ex situ non-contact scanning detection over a predetermined spectral range (infared) of said electromagnetic radiation passed through said liquid etchant, by means of a detector (24) over said at least at two points in time so as to detect at least one change in an at least one optical property of said liquid etchant; comparing said at least one change in said at least one optical property at said at least two

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points in time by means of an algorithm in a processor (26) so as to provide a concentration of the etchant.

It would have been obvious to one of ordinary skill in the art at the time of invention to use NIR measurement to measure HF concentration in the method of Brause et al. since Thompson et al. teach that the NIR technique is particularly well suited to quantification of HF over wide concentration and pH ranges such as in etching baths.

Regarding Claim 15, Thompson et al. teach that passing includes emitting electromagnetic radiation in a predetermined spectral range from an electromagnetic radiation source, transmitting said electromagnetic radiation via a first optical transmission element from said electromagnetic radiation source through a sampling element containing a sample of said liquid etchant, and conveying output electromagnetic radiation from said sample of said liquid etchant via a second optical transmission element to said detector.

Regarding Claim 16, Thompson et al. teach that comparing further comprises performing a chemometric manipulation on data relating to at least one change in said at least one optical property to provide the stripper concentration level.

Regarding Claims 17 and 19, Since Thompson teaches using the algorithm to determine concentration from the spectra data, and Brause teach that the etch rate correlates with concentration, it would have been obvious to one of ordinary skill in the art at the time of invention to determine the differential rate of change of etching using data for the change in concentration, a processor algorithm being an obvious expedient to one of ordinary skill in the art.

Regarding Claim 18, Thompson et al. teach that the algorithm further provides a rate of depletion of at least one chemical component of said liquid etchant over a period of time.

Regarding Claim 20, Brause et al teach a liquid etchant comprising ions halide ions (HF).

Regarding Claim 21, Thompson et al. teaches that passing the liquid etchant through a sampling element having a substantially transparent sampling tube.

Regarding Claim 22-24, Thompson et al. teach that the comparing step comprises converting one optical property change into a concentration rate of change of at least one chemical component of the liquid etchant.

Regarding Claim 25, the process limitations merely recite conventional steps for forming a calibration model from known reference data, well known in the art of data analysis using a spectrophotometer. Note that Brause et al. teach that oxide thickness measurements may be used to determine etch rates, and Thompson et al. teaches that a calibration model may be developed using a regression method and spectrum data aquired from samples irradiated with NIR.

Regarding Claim 26, Thompson et al. teach detecting a fault in a rate of addition of a replenishing chemical component.

Regarding Claims 28, the claim recites a confidence level that is inherently met by the prior art measuring procedures and instruments or else arises from essential limitations not provided for in the claims.

Regarding Claim 30, the method is independent of temperature.

Regarding Claim 32, Thompson et al. teach determining a concentration of an acid.

Regarding Claim 33, Thompson et al. teach a near-infared (NIR) light source.

Claims 27 and 29 are rejected under 35 U.S.C. 103(a) as being unpatentable over The publication "In-Situ Chemical Concentration Control for Wafer Wet Cleaning" to Brause et al. in view of The publication "Quantification of Hydrofluoric Acid Species by Chemical Modeling Regression of Near-Infrared Spectra" to Thompson et al. and in further view of JP 63307334 A to Nogami.

Regarding Claims 27 and 29, Brause et al. in view of Thompson et al. teaches the method of the invention substantially as claimed but does not expressly teach detecting bubbles.

However the step is old and well known in the art of making measurements with a spectrophotometer.

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data in the well known manner.

For example, JP 63307334 A to Nogami teaches a method of making a detection process independent of air bubbles. It would have been obvious to one of ordinary skill in the art at the time of invention to use a spectrophotometer superior in sensitivity in order to prevent irregularity in the sample

Regarding Claims 28, the claim recite a confidence level (95%) that is an inherent result of the prior art measuring procedures and instruments or else arises from essential limitations not provided for in the claims, since there are no recited manipulative differences.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Roberts Culbert whose telephone number is (571) 272-1433. The examiner can normally be reached on Monday-Friday (8:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Parviz Hassanzadeh can be reached on (571) 272-1435. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

MX

R. Culbert Examiner Art Unit 1763

Parviz Hassanzadeh

Supervisory Patent Examiner

Art Unit 1763